

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead-free

DESCRIPTION

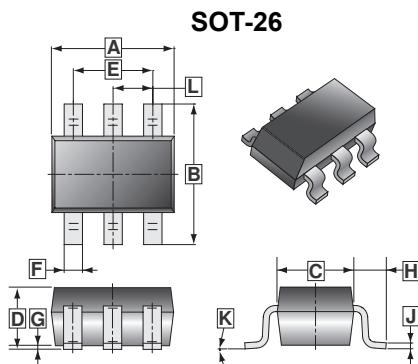
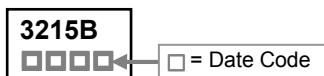
SST3215B provides designers with the best combination of fast switching, low on-resistance and cost-effectiveness.

SOT-26 package is universally used for all commercial-industrial surface mount applications.

FEATURES

- 150V/2.2A
- $R_{DS(ON)} \leq 320\text{m}\Omega @ V_{GS}=10\text{V}$
- $R_{DS(ON)} \leq 380\text{m}\Omega @ V_{GS}=4.5\text{V}$
- Reliable and rugged
- Green device available

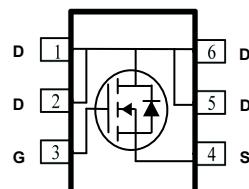
MARKING



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	0	0.10
B	2.60	3.00	H	0.60	REF.
C	1.40	1.80	I	0.12	REF.
D	1.30 MAX.		J	0°	10°
E	1.90	REF.	K	0.95	REF.
F	0.30	0.50	L		

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-26	3K	7 inch



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS}=10\text{V}$ ¹	I_D	2.2	A
		1.8	
		1.7	
		1.4	
Pulsed Drain Current ²	I_{DM}	8	A
Power Dissipation	P_D	3.2	W
		2	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating			
Thermal Resistance Junction to Ambient ¹	$t \leq 5\text{sec}$	62.5	°C / W
		125	
Thermal Resistance Junction to Ambient		156	
Thermal Resistance Junction to Case ¹	$R_{\theta JC}$	39	

ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	150	-	-	V	$\text{V}_{\text{GS}}=0$, $\text{I}_D=250\mu\text{A}$
Gate-Threshold Voltage	$\text{V}_{\text{GS(th)}}$	1	-	2.5	V	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}$, $\text{I}_D=250\mu\text{A}$
Gate-Body Leakage Current	I_{GSS}	-	-	± 100	nA	$\text{V}_{\text{GS}}=\pm 20\text{V}$
Drain-Source Leakage Current	I_{DSS}	-	-	1	μA	$\text{V}_{\text{DS}}=120\text{V}$, $\text{V}_{\text{GS}}=0$, $T_J=25^\circ\text{C}$
		-	-	10		$\text{V}_{\text{DS}}=120\text{V}$, $\text{V}_{\text{GS}}=0$, $T_J=55^\circ\text{C}$
		-	260	320	$\text{m}\Omega$	$\text{V}_{\text{GS}}=10\text{V}$, $\text{I}_D=1.5\text{A}$
Drain-Source On-Resistance ³	$\text{R}_{\text{DS(ON)}}$	-	290	380		$\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=1.5\text{A}$
Forward Transfer conductance	g_{fs}	-	3.3	-	S	$\text{V}_{\text{DS}}=15\text{V}$, $\text{I}_D=1\text{A}$
Total Gate Charge	Q_g	-	8.1	-	nC	$\text{V}_{\text{DS}}=75\text{V}$
Gate-Source Charge	Q_{gs}	-	1	-		$\text{V}_{\text{GS}}=10\text{V}$
Gate-Drain ("Miller")Charge	Q_{gd}	-	1.9	-		$\text{I}_D=1.7\text{A}$
Turn-on Delay Time	$\text{T}_{\text{d(on)}}$	-	5.2	-	nS	$\text{V}_{\text{DS}}=75\text{V}$
Rise Time	T_r	-	16.2	-		$\text{V}_{\text{GS}}=10\text{V}$
Turn-off Delay Time	$\text{T}_{\text{d(off)}}$	-	20.8	-		$\text{R}_G=6\Omega$
Fall Time	T_f	-	15.6	-		$\text{I}_D=1\text{A}$
Input Capacitance	C_{iss}	-	298	-	pF	$\text{V}_{\text{GS}}=0\text{V}$
Output Capacitance	C_{oss}	-	32	-		$\text{V}_{\text{DS}}=30\text{V}$
Reverse Transfer Capacitance	C_{rss}	-	19	-		$f=1\text{MHz}$

Source-Drain Diode Characteristic

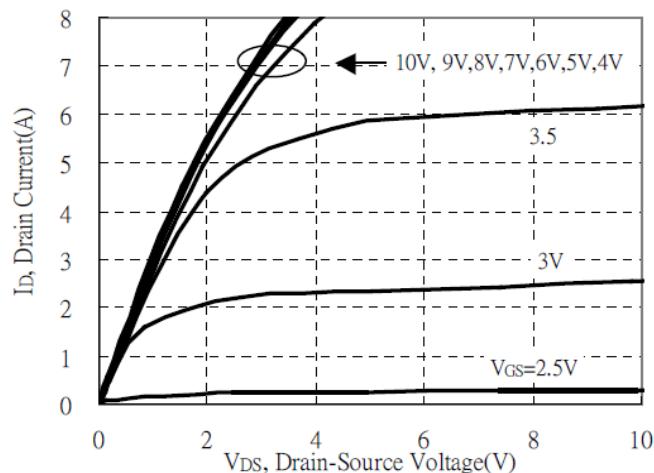
Diode Forward Voltage ³	V_{SD}	-	-	1.2	V	$\text{I}_S=1.7\text{A}$, $\text{V}_{\text{GS}}=0$
Continuous Source Current ¹	I_S	-	-	1.7	A	$\text{I}_F=1.7\text{A}$, $d\text{I}/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$
Pulsed Source Current ²	I_{SM}	-	-	5		
Reverse Recovery Time	T_{RR}	-	45	-	nS	$\text{I}_F=1.7\text{A}$, $d\text{I}/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$
Reverse Recovery Charge	Q_{RR}	-	16	-		

Notes:

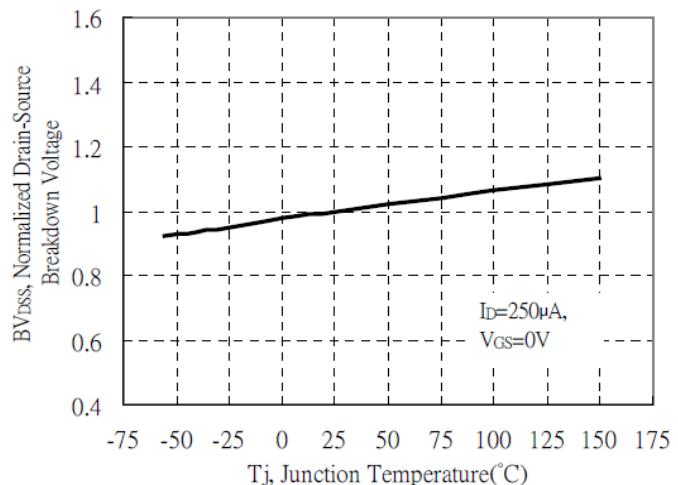
1. Surface mounted on 1 inch² FR4 board with 2 oz copper.
2. The power dissipation is limited by 150°C junction temperature.
3. The data is tested by pulse: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

CHARACTERISTIC CURVES

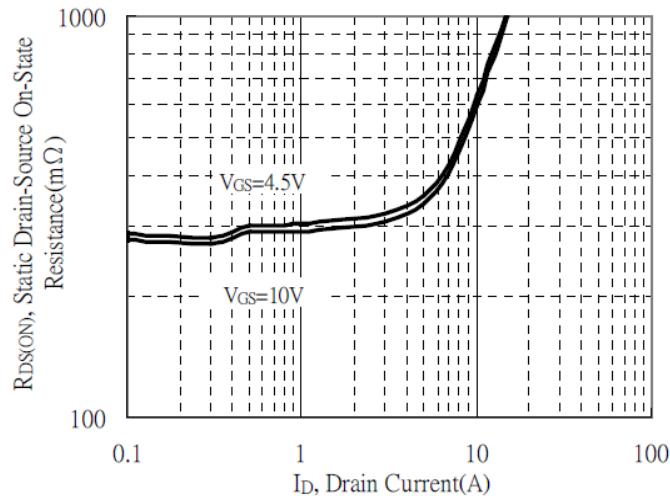
Typical Output Characteristics



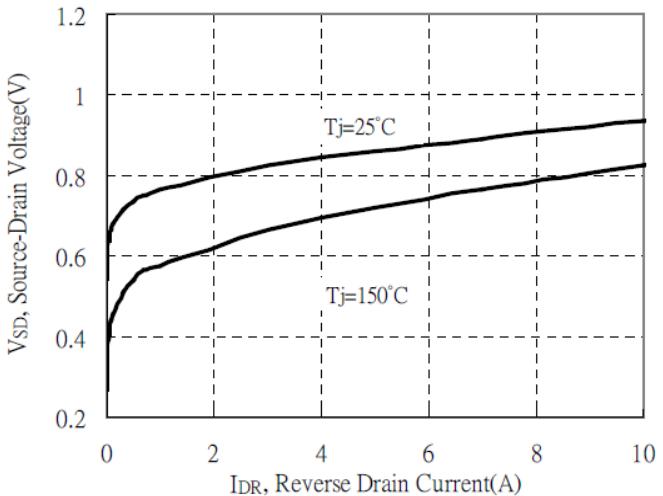
Breakdown Voltage vs Ambient Temperature



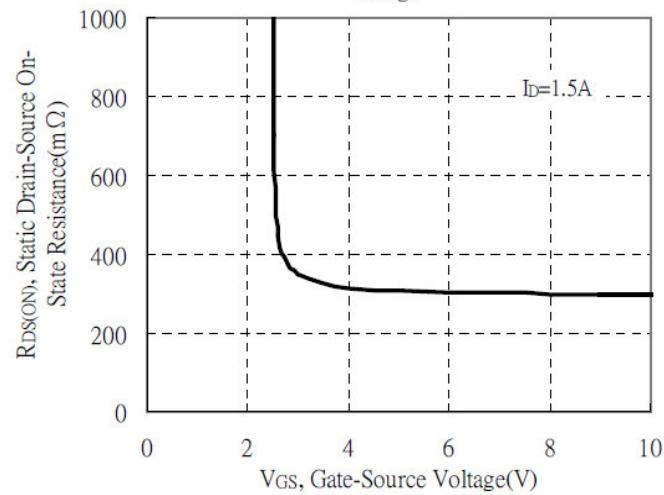
Static Drain-Source On-State resistance vs Drain Current



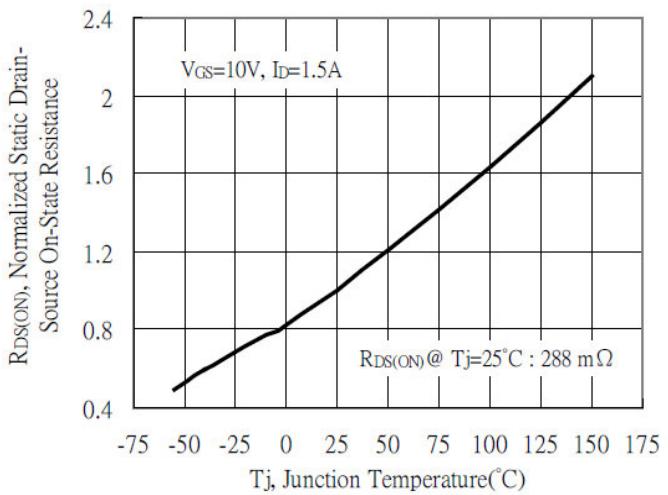
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

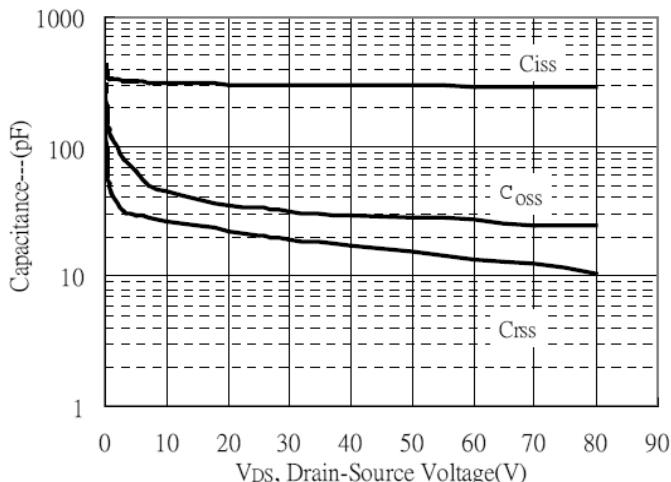


Drain-Source On-State Resistance vs Junction Temperature

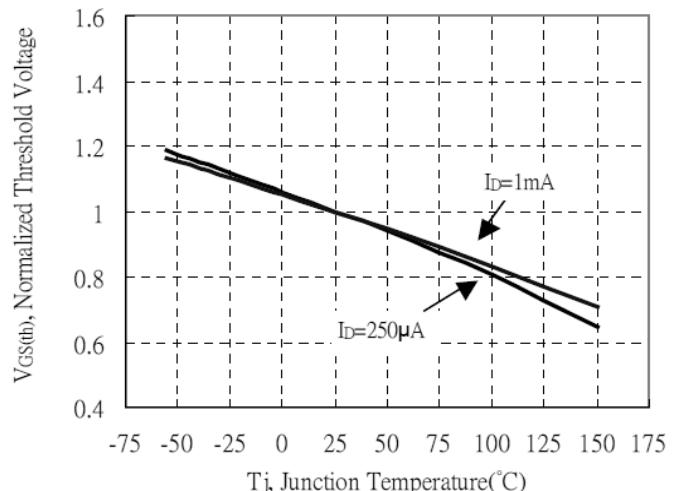


CHARACTERISTIC CURVES

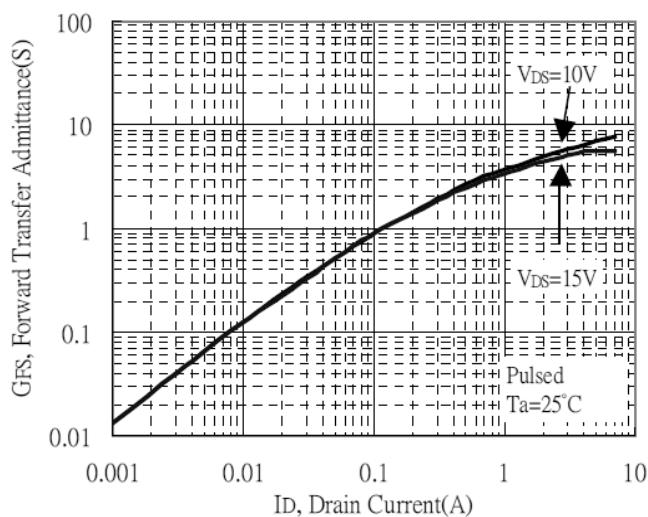
Capacitance vs Drain-to-Source Voltage



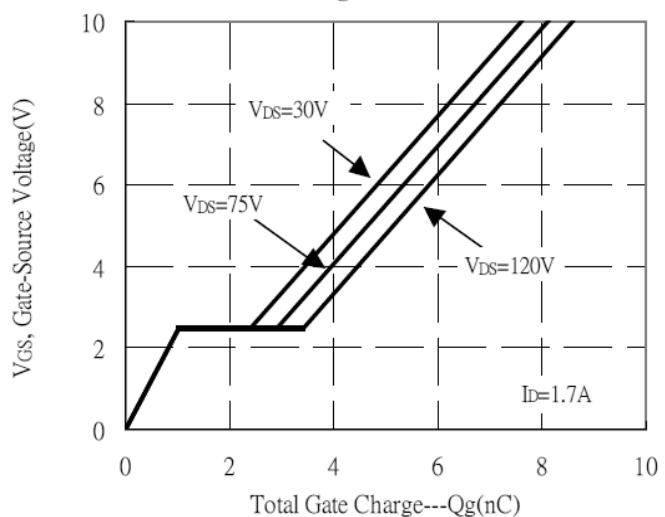
Threshold Voltage vs Junction Temperature



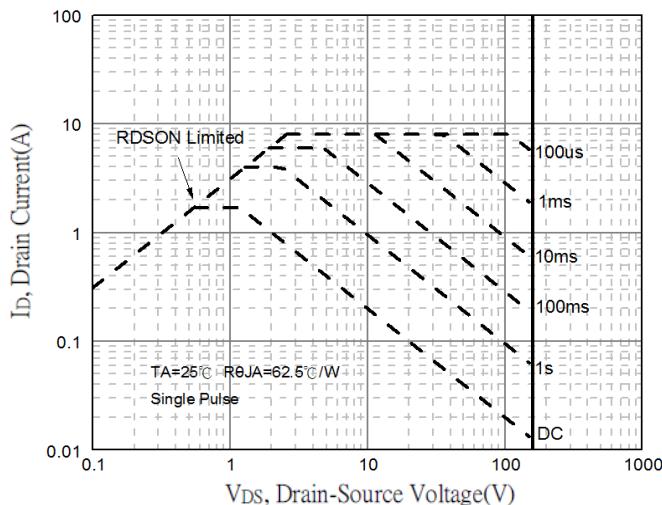
Forward Transfer Admittance vs Drain Current



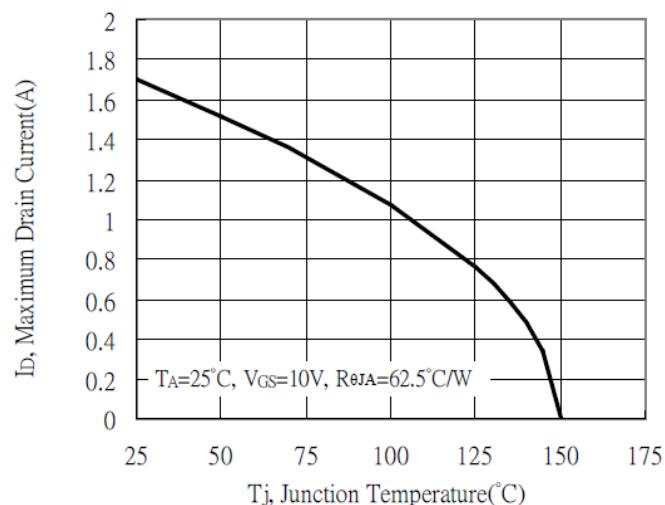
Gate Charge Characteristics



Maximum Safe Operating Area

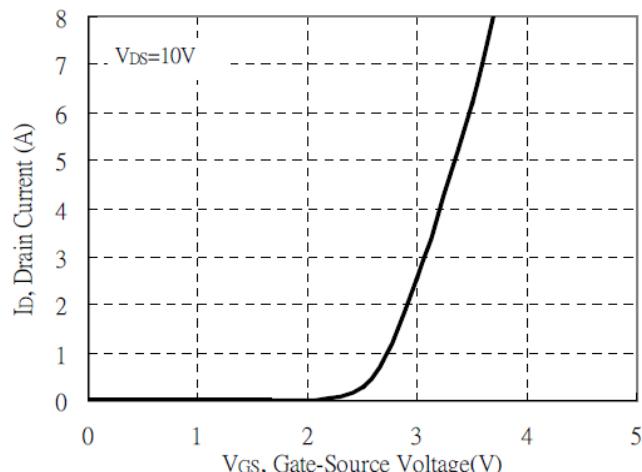


Maximum Drain Current vs Junction Temperature

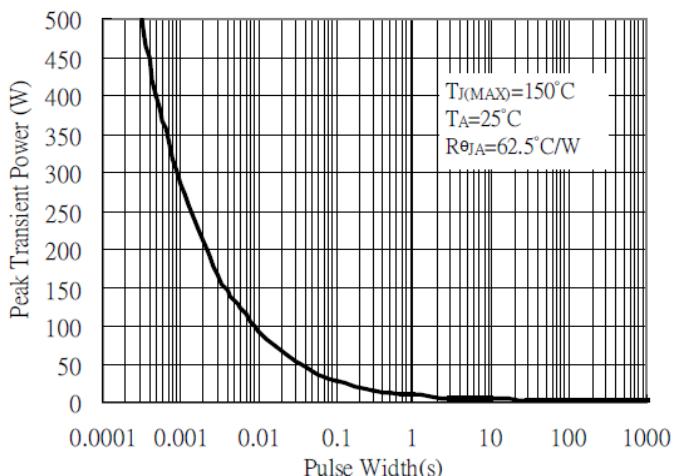


CHARACTERISTIC CURVES

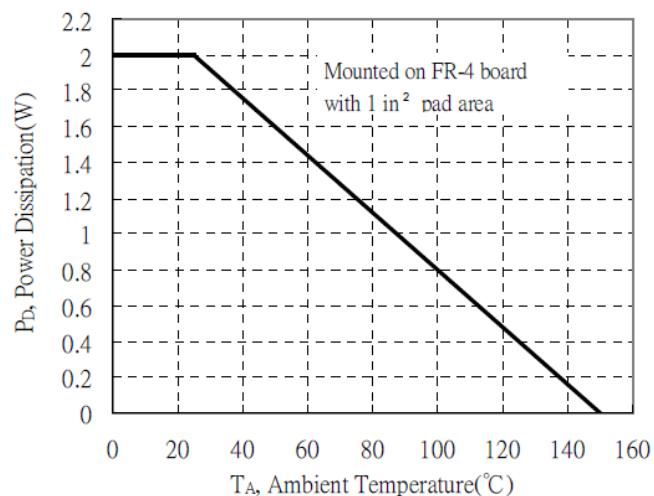
Typical Transfer Characteristics



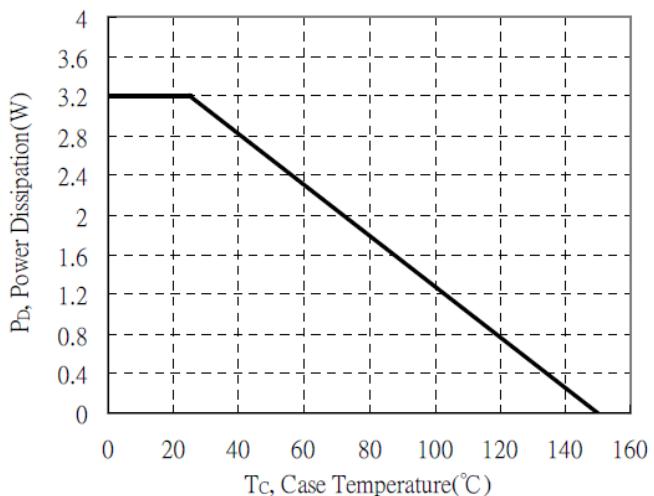
Single Pulse Maximum Power Dissipation



Power Derating Curve



Power Derating Curve



Transient Thermal Response Curves

